

NP60N06VLK

60 V – 60 A – N-channel Power MOS FET

Application: Automotive

R07DS1339EJ0100

Rev.1.00

Apr 8, 2016

Description

NP60N06VLK is N-channel MOS Field Effect Transistor designed for high current switching applications.

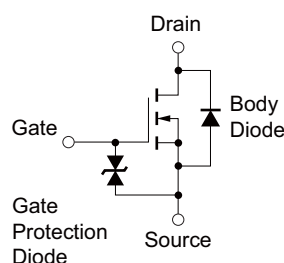
Features

- Super low on-state resistance
— $R_{DS(on)1} = 7.9 \text{ m}\Omega \text{ MAX.}$ ($V_{GS} = 10 \text{ V}$, $I_D = 30 \text{ A}$)
- Low C_{iss} : $C_{iss} = 2400 \text{ pF TYP.}$ ($V_{DS} = 25 \text{ V}$)
- Designed for automotive application and AEC-Q101 qualified

Outline



TO-252(MP-3ZP)



Equivalent circuit

Remark: Strong electric field, when exposed to this device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred.

Ordering Information

Part No.	Lead Plating	Packing		Package
NP60N06VLK-E1-AY ^{*1}	Pure Sn (Tin)	Tape 800 p/reel	Taping (E1 type)	TO-252(MP-3ZP)
NP60N06VLK-E2-AY ^{*1}			Taping (E2 type)	

Note: ^{*1}. Pb-free (This product does not contain Pb in the external electrode)

Absolute Maximum Ratings ($T_A = 25^\circ\text{C}$)

Item	Symbol	Ratings	Unit
Drain to Source Voltage ($V_{GS} = 0\text{ V}$)	V_{DSS}	60	V
Gate to Source Voltage ($V_{DS} = 0\text{ V}$)	V_{GSS}	± 20	V
Drain Current (DC) ($T_C = 25^\circ\text{C}$)	$I_{D(DC)}$	± 60	A
Drain Current (pulse) ^{*1}	$I_{D(pulse)}$	± 240	A
Total Power Dissipation ($T_C = 25^\circ\text{C}$)	P_{T1}	105	W
Total Power Dissipation ($T_A = 25^\circ\text{C}$)	P_{T2}	1.2	W
Channel Temperature	T_{ch}	175	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to $+175$	$^\circ\text{C}$
Repetitive Avalanche Current ^{*2}	I_{AR}	25	A
Repetitive Avalanche Energy ^{*2}	E_{AR}	63	mJ

Notes: *1. $T_C = 25^\circ\text{C}$, $PW \leq 10\text{ }\mu\text{s}$, Duty Cycle $\leq 1\%$

*2. $R_G = 25\text{ }\Omega$, $V_{GS} = 20\text{ V} \rightarrow 0\text{ V}$

Thermal Resistance

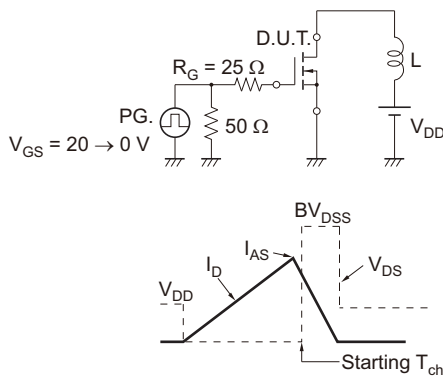
Channel to Case Thermal Resistance	$R_{th(ch-C)}$	1.43	$^\circ\text{C/W}$
Channel to Ambient Thermal Resistance	$R_{th(ch-A)}$	125	$^\circ\text{C/W}$

Electrical Characteristics (T_A = 25°C)

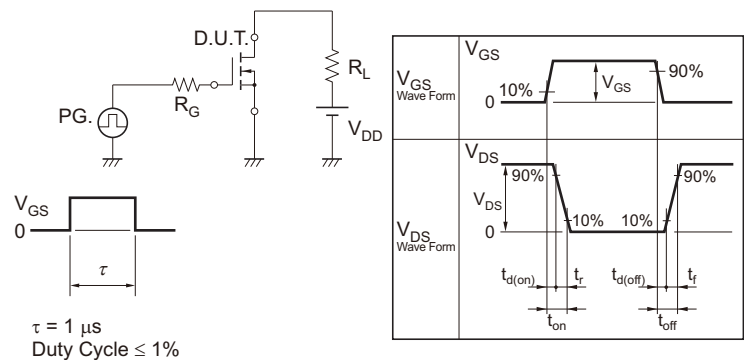
Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Zero Gate Voltage Drain Current	I _{DSS}			1	μA	V _{DS} = 60 V, V _{GS} = 0 V
Gate Leakage Current	I _{GSS}			±10	μA	V _{GS} = ±20 V, V _{DS} = 0 V
Gate to Source Threshold Voltage	V _{GS(th)}	1.5	2.1	2.5	V	V _{DS} = V _{GS} , I _D = 250 μA
Forward Transfer Admittance *1	y _{fs}	33	54		S	V _{DS} = 5 V, I _D = 30 A
Drain to Source On-state Resistance *1	R _{DS(on)1}		6.1	7.9	mΩ	V _{GS} = 10 V, I _D = 30 A
	R _{DS(on)2}		7.4	12.0	mΩ	V _{GS} = 4.5 V, I _D = 15 A
Input Capacitance	C _{iss}		2400	3600	pF	V _{DS} = 25 V, V _{GS} = 0 V, f = 1 MHz
Output Capacitance	C _{oss}		230	350	pF	
Reverse Transfer Capacitance	C _{rss}		80	150	pF	
Turn-on Delay Time	t _{d(on)}		18	40	ns	V _{DD} = 30 V, I _D = 30 A, V _{GS} = 10 V, R _G = 0 Ω
Rise Time	t _r		6	20	ns	
Turn-off Delay Time	t _{d(off)}		45	90	ns	
Fall Time	t _f		3	10	ns	
Total Gate Charge	Q _G		37	56	nC	V _{DD} = 48 V, V _{GS} = 10 V, I _D = 60 A
Gate to Source Charge	Q _{GS}		9		nC	
Gate to Drain Charge	Q _{GD}		8		nC	
Body Diode Forward Voltage *1	V _{F(S-D)}		0.9	1.5	V	I _F = 60 A, V _{GS} = 0 V
Reverse Recovery Time	t _{rr}		32		ns	I _F = 60 A, V _{GS} = 0 V, di/dt = 100 A/μs
Reverse Recovery Charge	Q _{rr}		30		nC	

Note: *1. Pulsed test

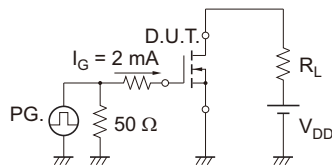
TEST CIRCUIT 1 AVALANCHE CAPABILITY



TEST CIRCUIT 2 SWITCHING TIME

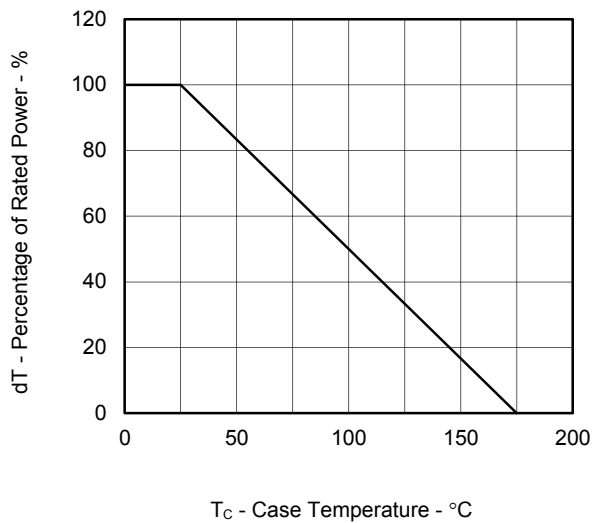


TEST CIRCUIT 3 GATE CHARGE

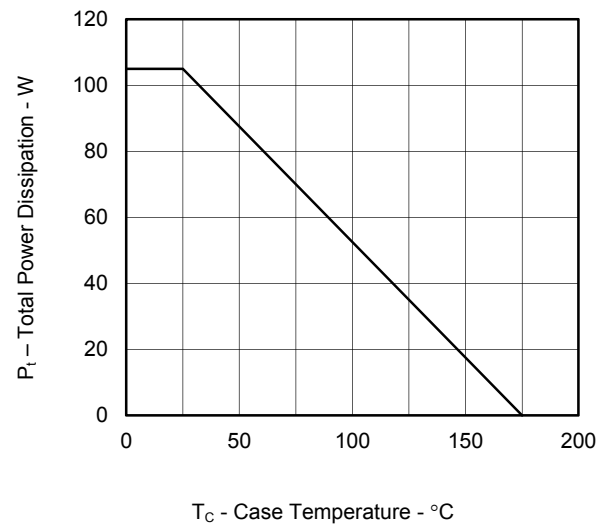


Typical Characteristics ($T_A = 25^\circ\text{C}$)

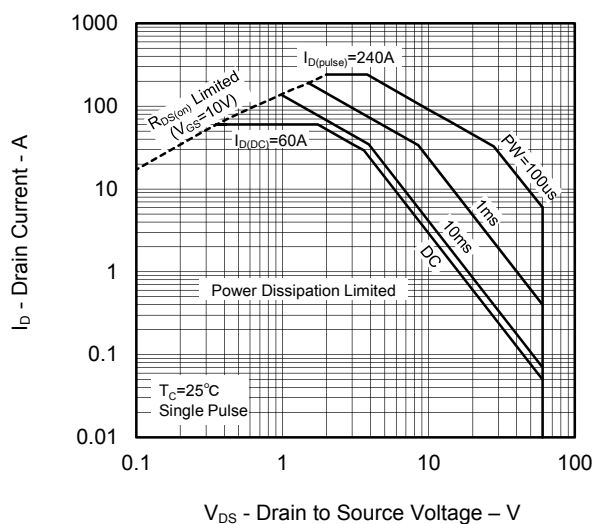
DERATING FACTOR OF FORWARD BIAS SAFE OPERATING AREA



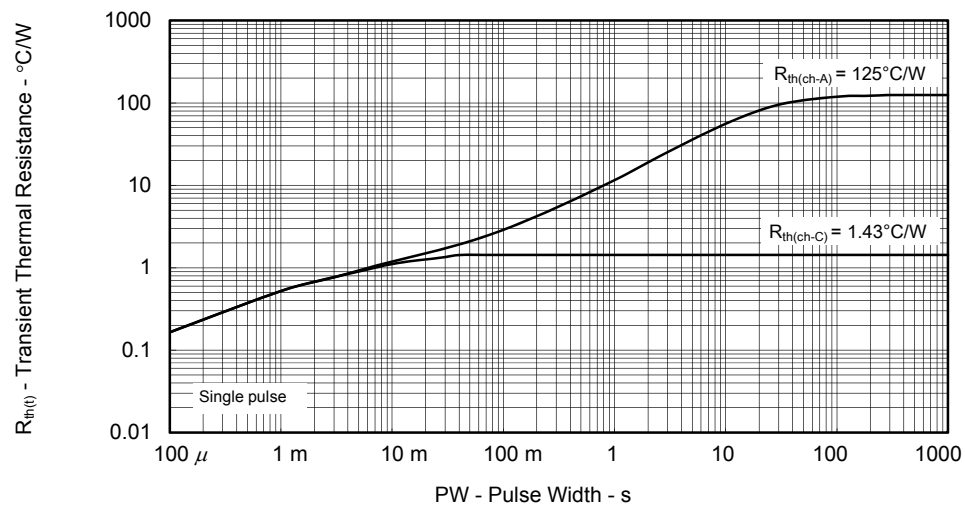
TOTAL POWER DISSIPATION vs. CASE TEMPERATURE

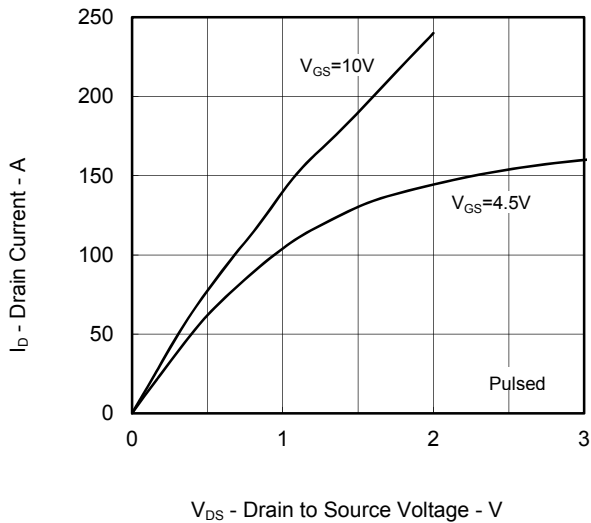


FORWARD BIAS SAFE OPERATING AREA

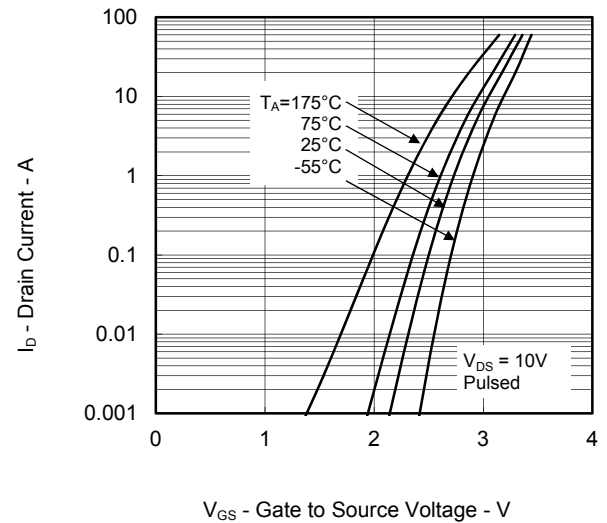
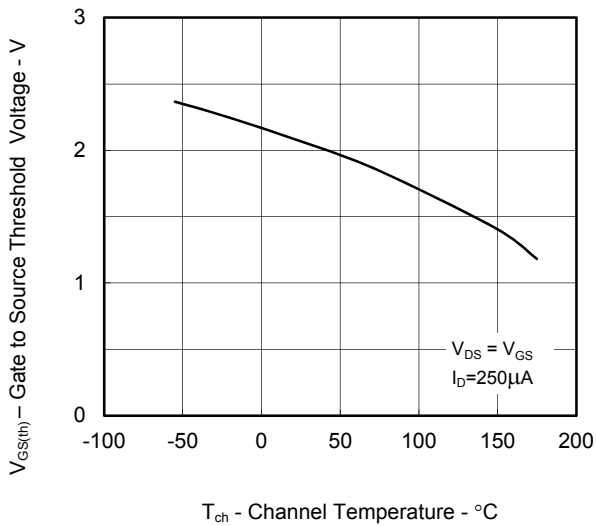
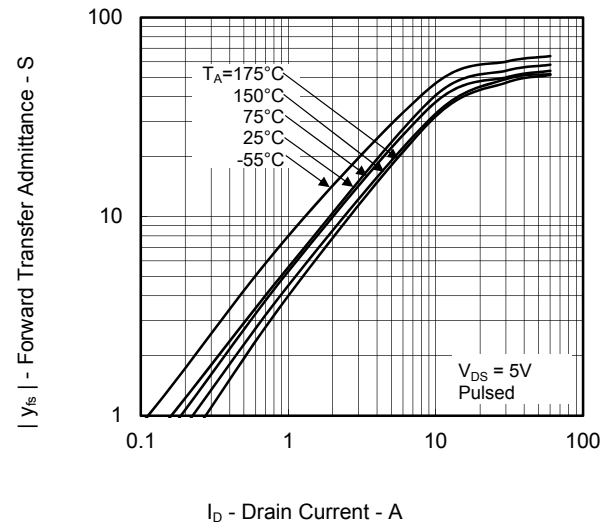
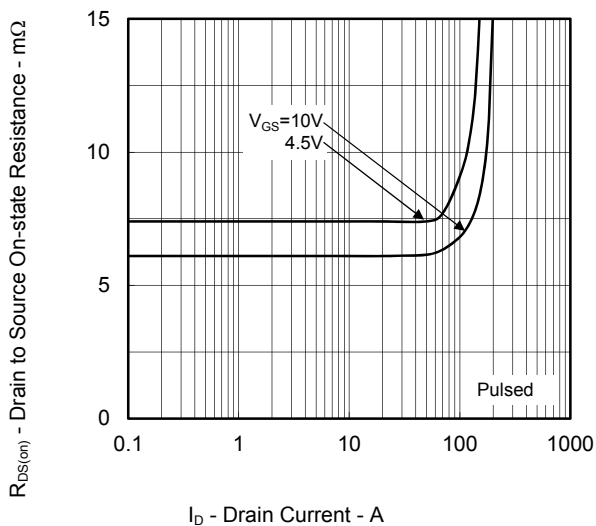
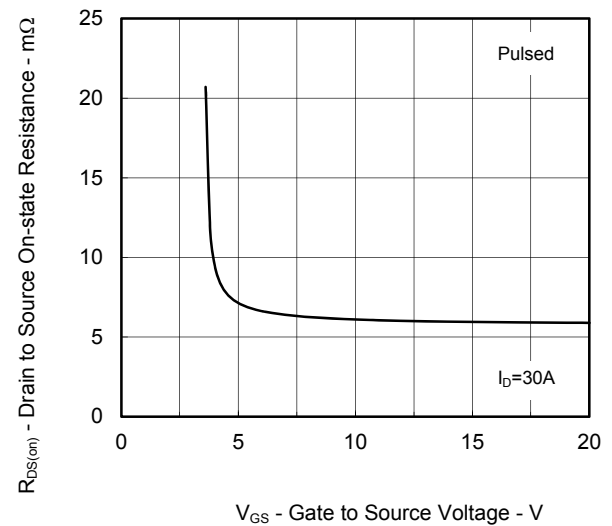


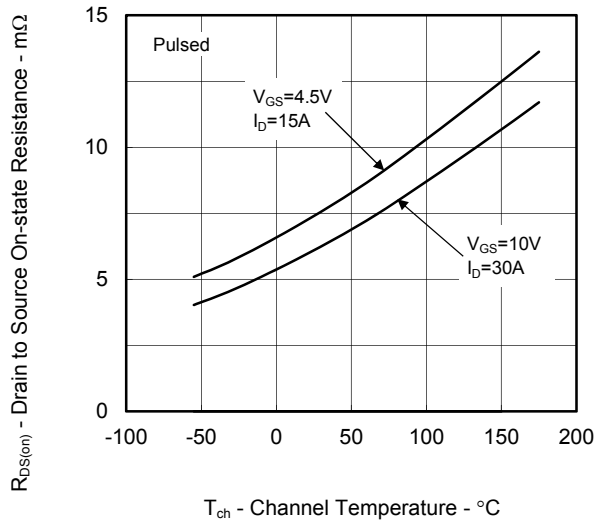
TRANSIENT THERMAL RESISTANCE vs. PULSE WIDTH



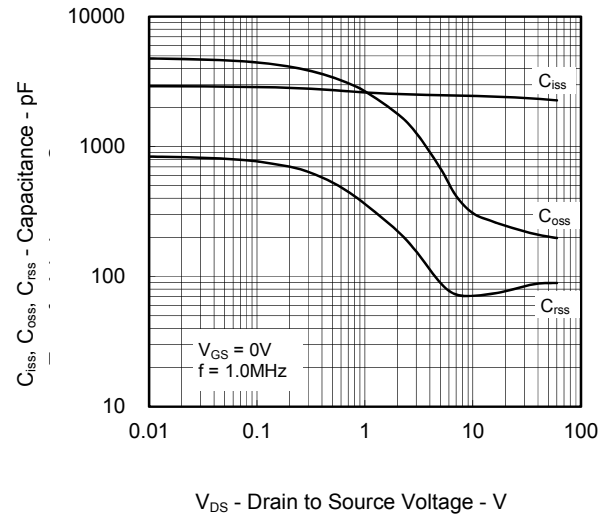
DRAIN CURRENT vs.
DRAIN TO SOURCE VOLTAGE

FORWARD TRANSFER CHARACTERISTICS

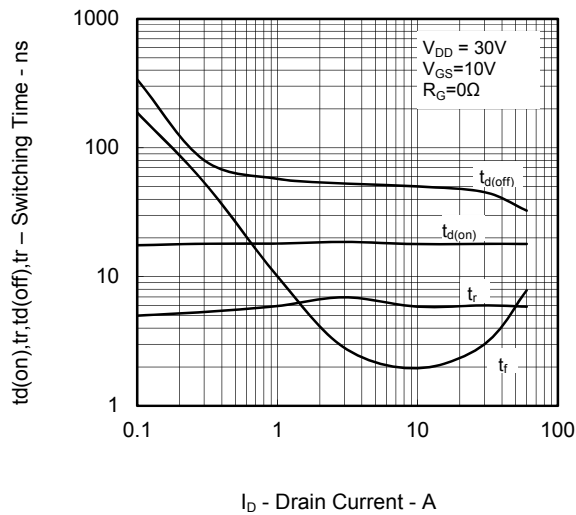
GATE TO SOURCE THRESHOLD VOLTAGE vs.
CHANNEL TEMPERATUREFORWARD TRANSFER ADMITTANCE vs. DRAIN
CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
DRAIN CURRENTDRAIN TO SOURCE ON-STATE RESISTANCE vs.
GATE TO SOURCE VOLTAGE

DRAIN TO SOURCE ON-STATE RESISTANCE vs.
CHANNEL TEMPERATURE

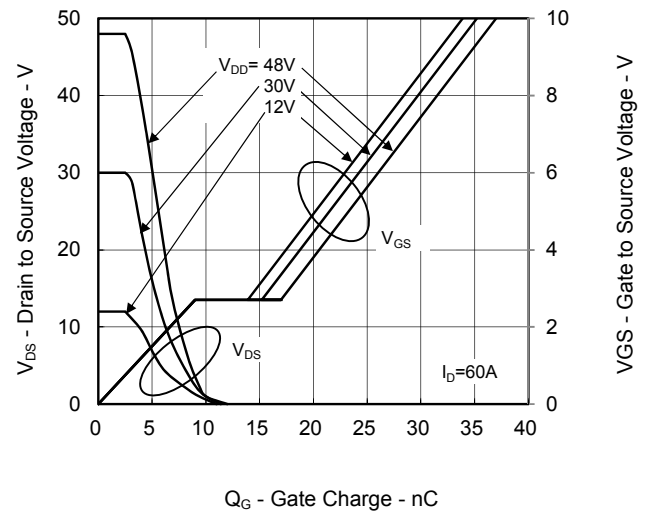
CAPACITANCE vs. DRAIN TO SOURCE VOLTAGE



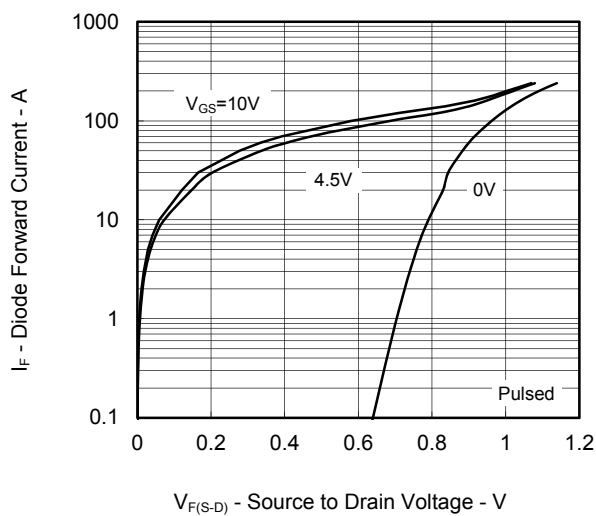
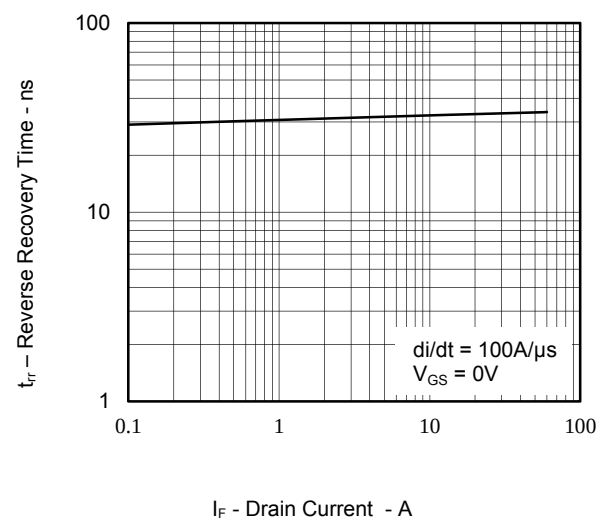
SWITCHING CHARACTERISTICS



DYNAMIC INPUT CHARACTERISTICS

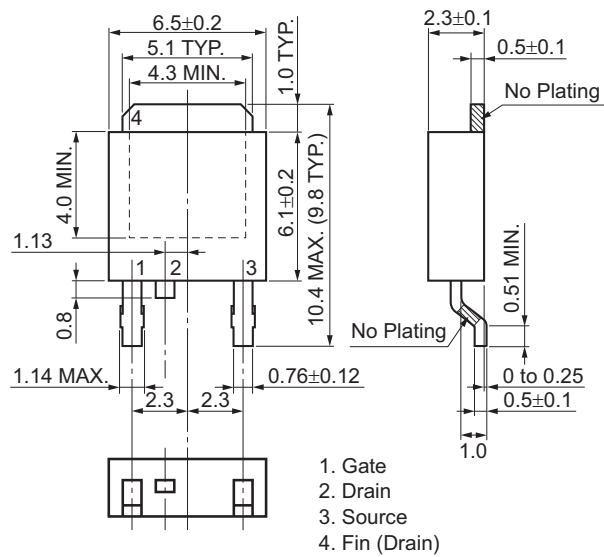


SOURCE TO DRAIN DIODE FORWARD VOLTAGE

REVERSE RECOVERY TIME vs.
DRAIN CURRENT

Package Drawings (Unit: mm)**TO-252 (MP-3ZP) (Mass: 1.48 g TYP.)**

Renesas package code: PRSS0004ZP-A



Revision History	NP60N06VLK Data Sheet
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Rev.	Date	Description	
		Page	Summary
1.00	Apr. 8, 2016	—	First Edition Issued

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